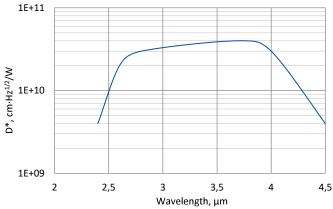


PVI-4-1×1-T039-NW-36

$2.4-4.5\ \mu\text{m}$ HgCdTe ambient temperature, optically immersed photovoltaic detector

PVI-4-1×1-TO39-NW-36 is uncooled IR photovoltaic detector based on sophisticated HgCdTe heterostructure for the best performance and stability. The device is optimized for the maximum performance at 4 µm. Detector element is monolithically integrated with hyperhemispherical GaAs microlens in order to improve performance of the device. Reverse bias may significantly increase response speed and dynamic range. It also results in improved performance at high frequencies, but 1/f noise that appears in biased devices may reduce performance at low frequencies

Spectral response (T_a = 20°C, V_b = 0 mV)





Exemplary spectral detectivity, the spectral response of delivered devices may differ.

Specification ($T_a = 20^{\circ}C$, $V_b = 0 \text{ mV}$)

| Parameter | Detector type |
|--|----------------------------------|
| | PVI-4-1×1-TO39-NW-36 |
| Active element material | epitaxial HgCdTe heterostructure |
| Cut-on wavelength λ_{cut-on} (10%), μm | 2.4±0.5 |
| Peak wavelength λ_{peak} , μm | 3.4±0.5 |
| Optimum wavelength λ_{opt} , μ m | 4.0 |
| Cut-off wavelength $\lambda_{cut-off}$ (10%), μm | 4.5±0.3 |
| Detectivity D*(λ_{peak}), cm ⁻ Hz ^{1/2} /W | ≥4 . 0×10 ¹⁰ |
| Detectivity D*(λ_{opt}), cm ⁻ Hz ^{1/2} /W | ≥3.0×10 ¹⁰ |
| Current responsivity $R_i(\lambda_{peak})$, A/W | ≥2.0 |
| Current responsivity $R_i(\lambda_{opt})$, A/W | ≥1.0 |
| Time constant τ, ns | ≤150 |
| Resistance R, Ω | ≥600 |
| Optical area A ₀ , mm×mm | 1×1 |
| Package | ТО39 |
| Acceptance angle Φ | ~36° |
| Window | none |

Features

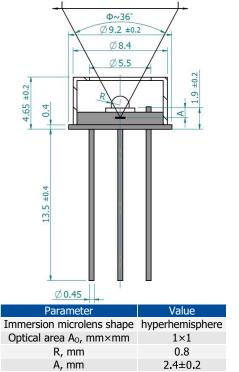
- Wide dynamic range
- Convenient to use
- Very small size
- Cost-effective solution
- Quantity discounted price
- Fast delivery

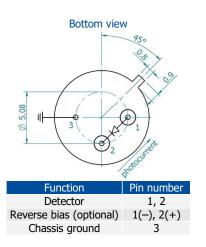
Applications

- Gas detection, monitoring and analysis (CH₄, C₂H₂, CH₂O, HCl, NH₃, SO₂, C₂H₆)
- Breath analysis
- Explosion prevention
- Flue gas denitrification
- Emission control (exhaust fumes, greenhouse gases)



Mechanical layout, mm





 Φ – acceptance angle R – hyperhemisphere microlens radius

A - distance from the bottom of hyperhemisphere microlens to the focal plane

Precautions for use and storage

- Standard ohmmeter may overbias and damage the detector. Bias of 10 mV can be used for resistance measurements.
- Operation in 10% to 80% humidity and -20°C to 30°C ambient temperature.
- Beam power limitations for optically immersed detector:
 - $_{\circ}$ irradiance with CW or single pulse longer than 1 μ s irradiance on the apparent optical active area must not exceed 2.5 W/cm²,
 - o irradiance of the pulse shorter than 1 μs must not exceed 10 kW/cm².
- Storage in dark place with 10% to 90% humidity and -20°C to 50°C ambient temperature.